[POWER CONNECTION OF CIRCUIT]

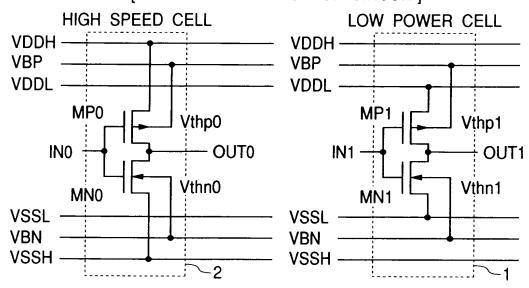
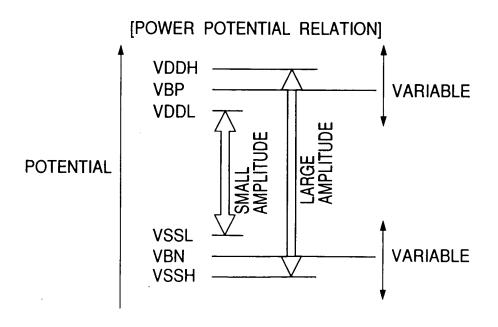


FIG. 2



[INCREASE IN THRESHOLD VOLTAGE BY APPLICATION OF SUBSTRATE BIAS]

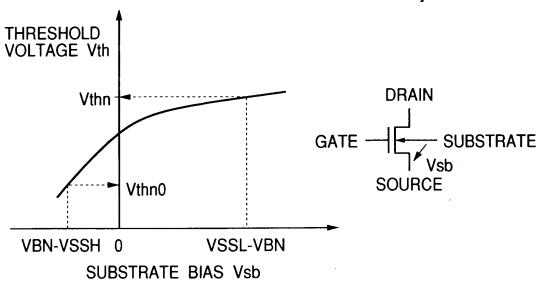
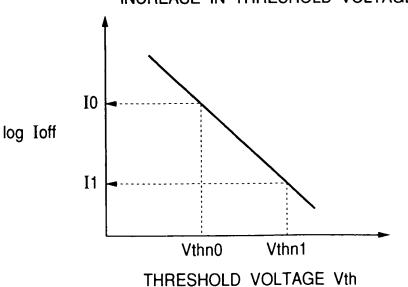


FIG. 4

[DECREASE IN LEAK CURRENT BY INCREASE IN THRESHOLD VOLTAGE]



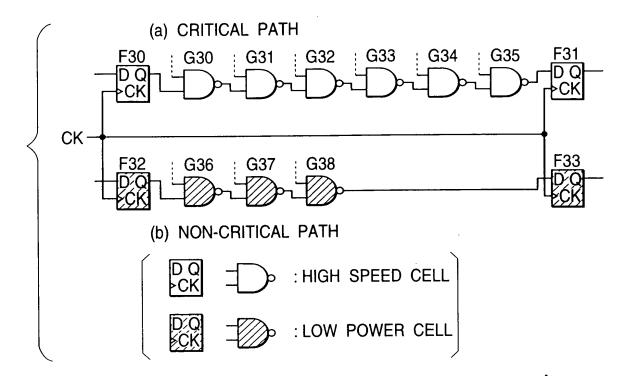
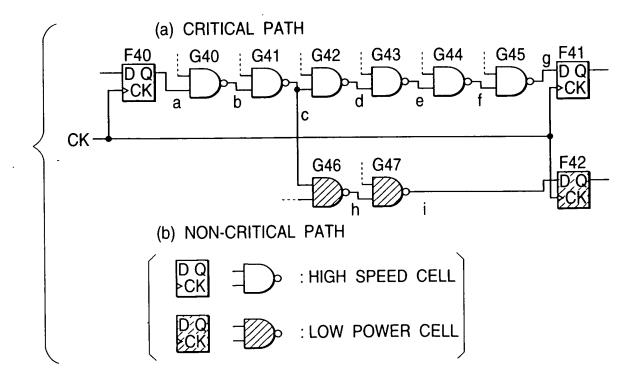
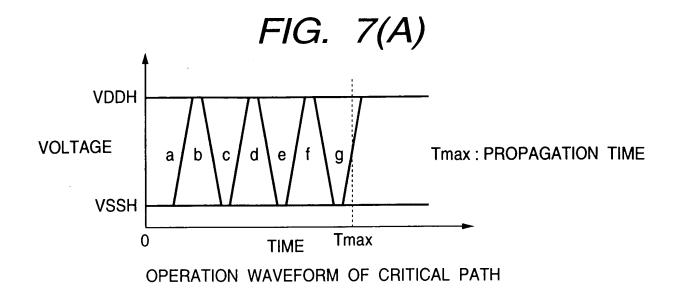


FIG. 6





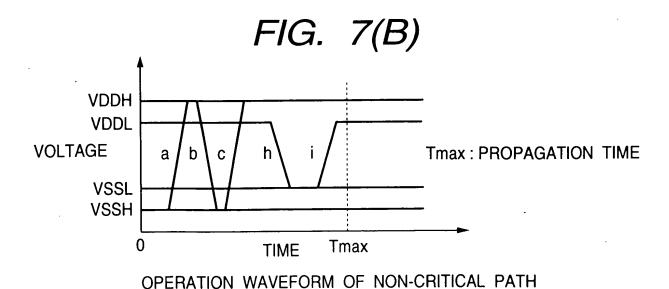


FIG. 8

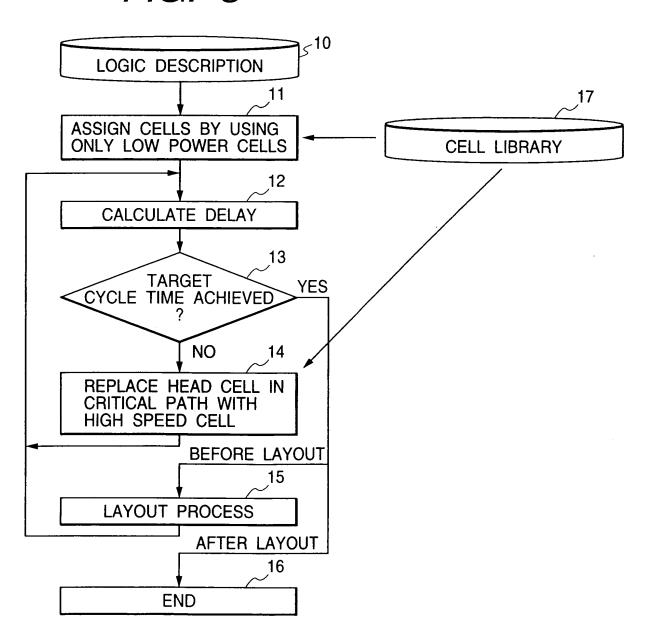


FIG. 9(A)

[CASE USING ONLY LOW POWER CELLS]

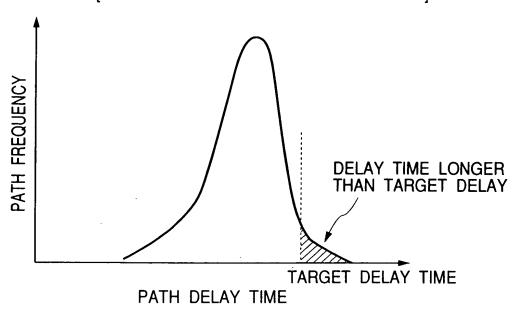


FIG. 9(B)

[CASE USING HIGH SPEED CELL FOR CRITICAL PATH]

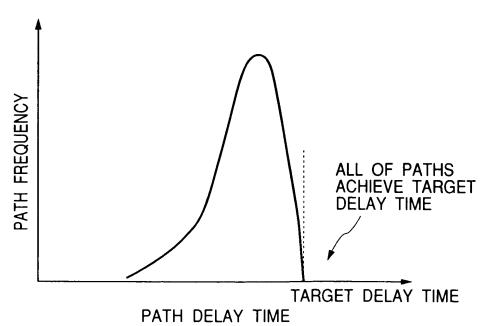


FIG. 10(A)

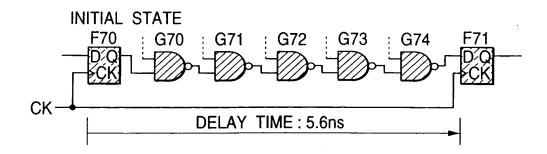


FIG. 10(B)

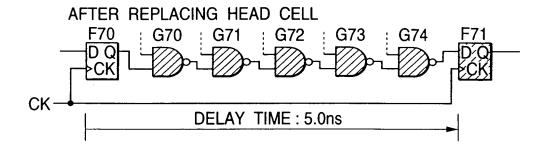


FIG. 10(C)

AFTER COMPLETION OF REPLACEMENT

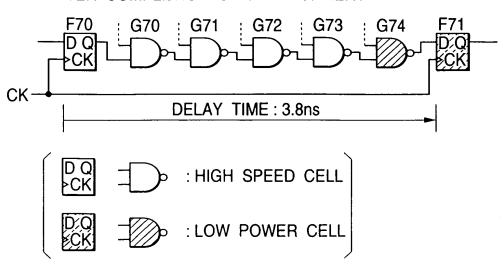
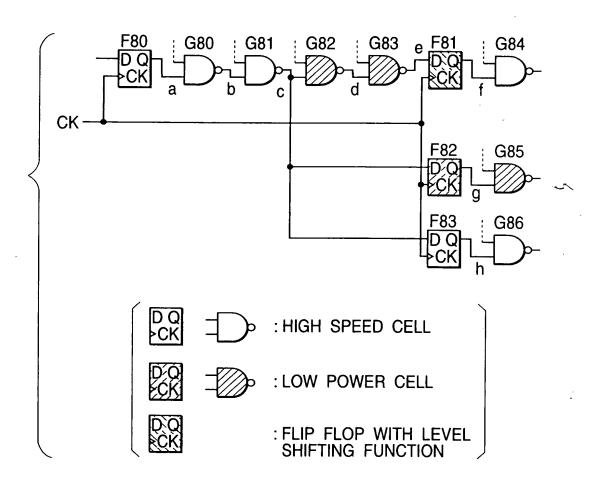


FIG. 11



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FIG. 12

[FLIP FLOP WITH LEVEL SHIFTING FUNCTION]

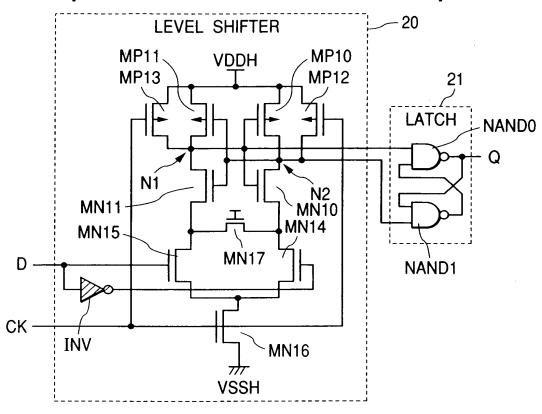


FIG. 13

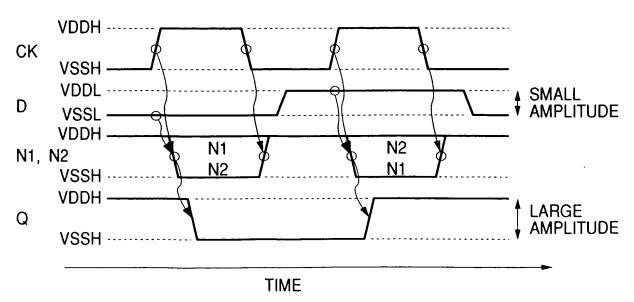


FIG. 14

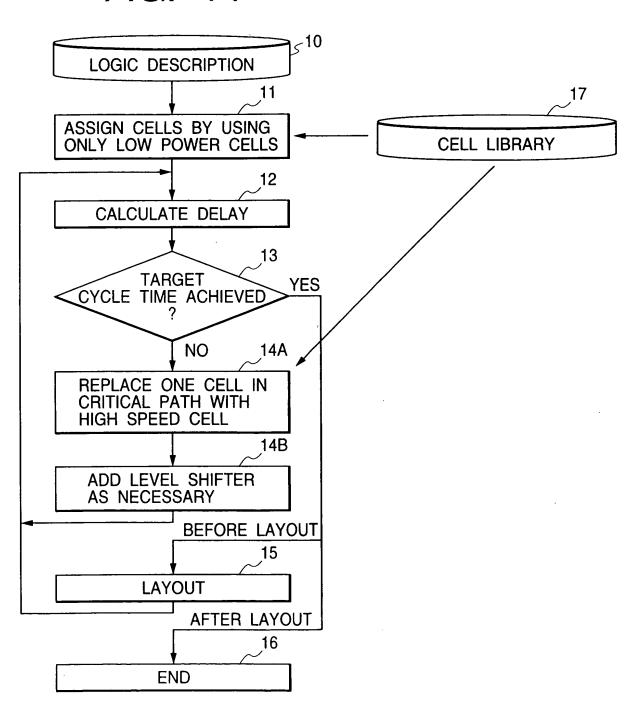


FIG. 15(A)

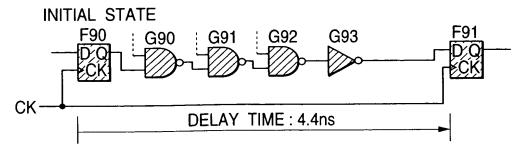


FIG. 15(B)

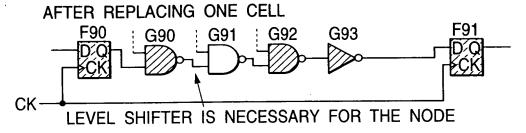


FIG. 15(C)

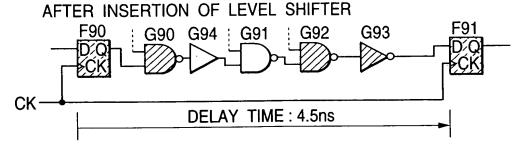
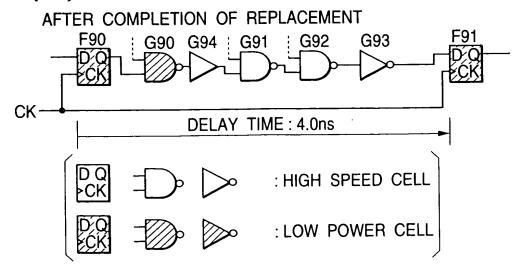
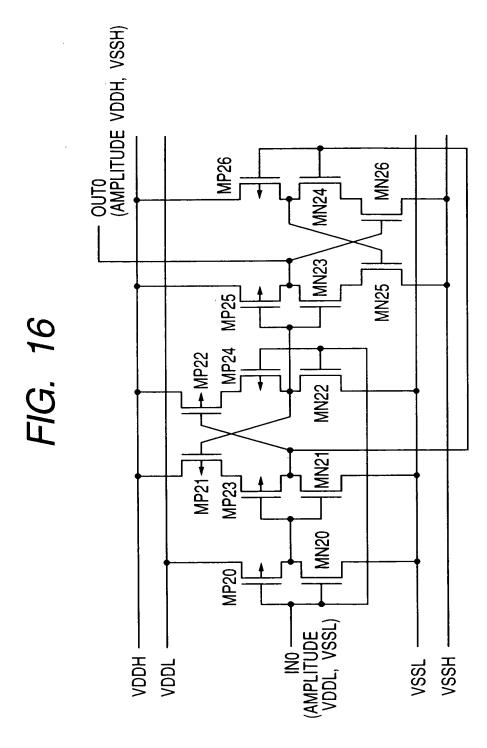
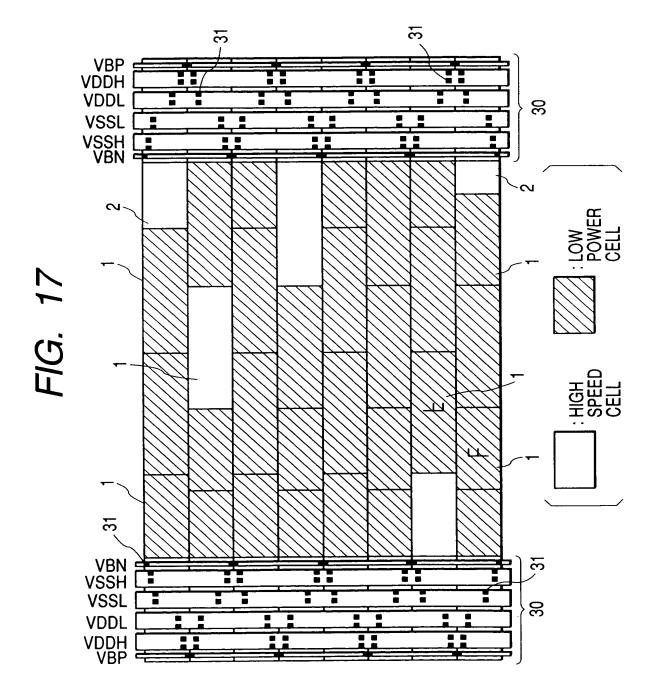


FIG. 15(D)



19 c,





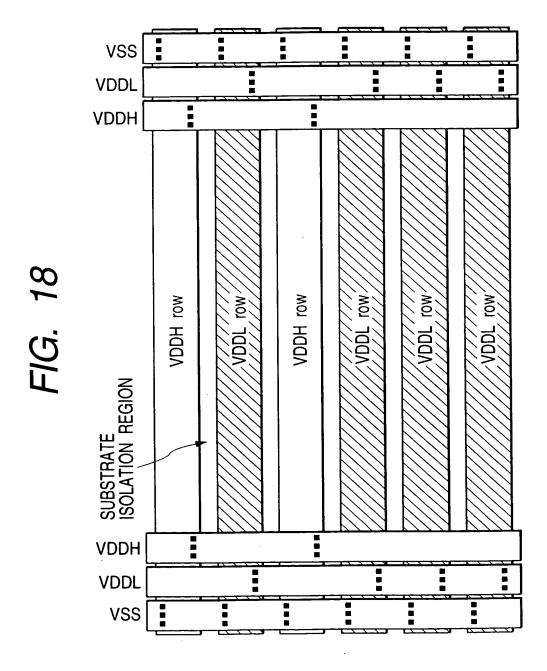


FIG. 19(A)

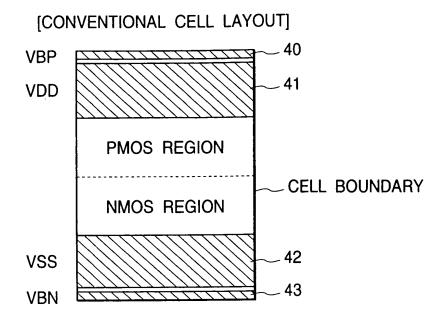
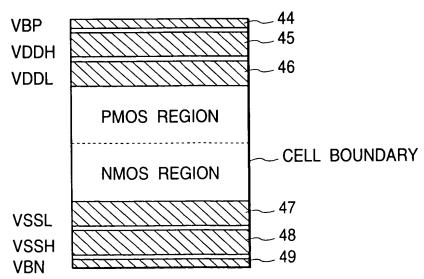
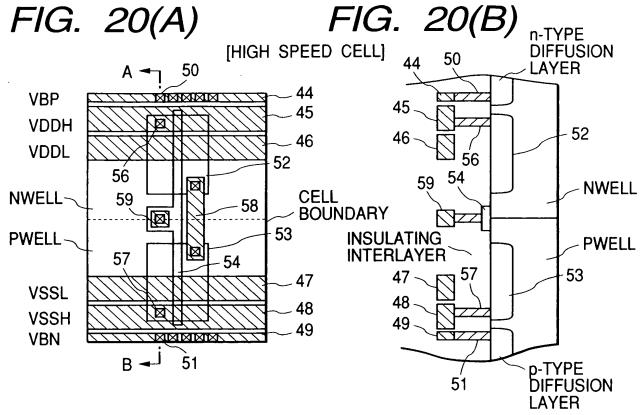
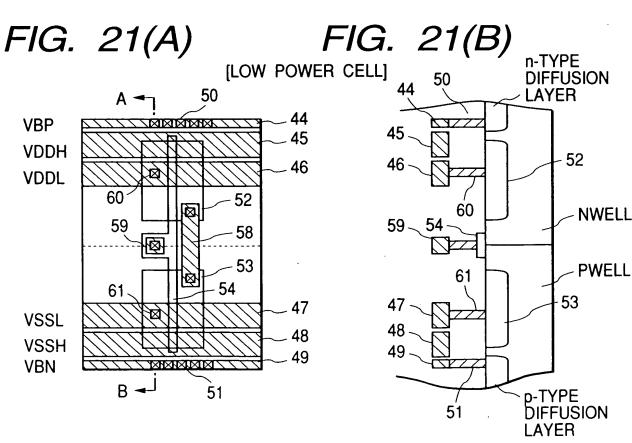


FIG. 19(B)

[CELL LAYOUT OF THE INVENTION]







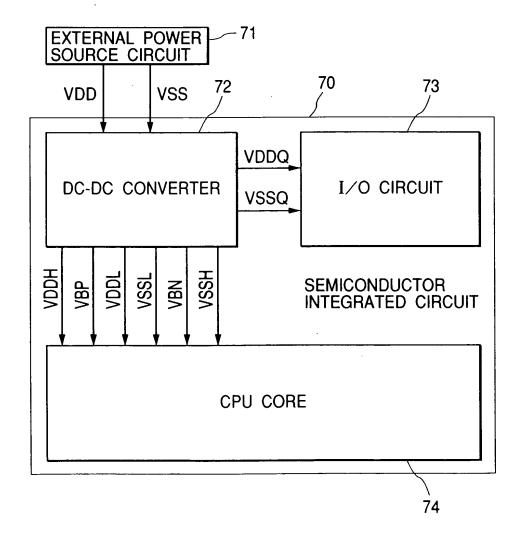


FIG. 23

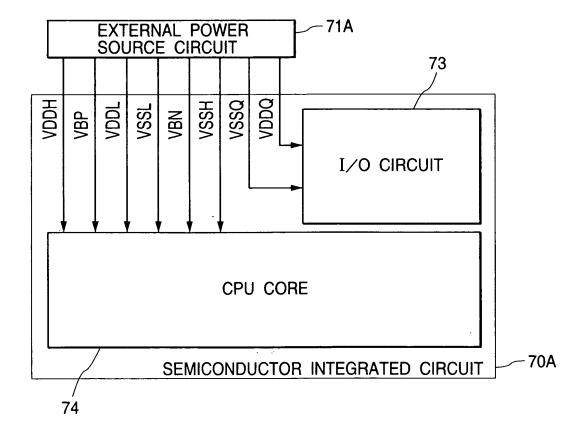
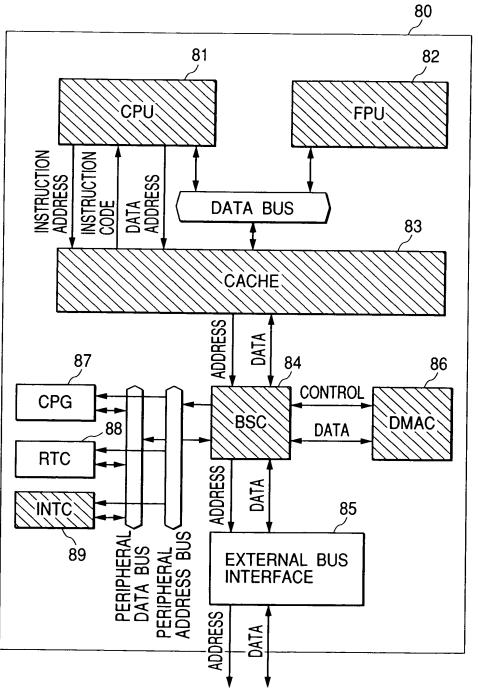


FIG. 24



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FIG. 25

[POWER CONNECTION OF CIRCUIT]

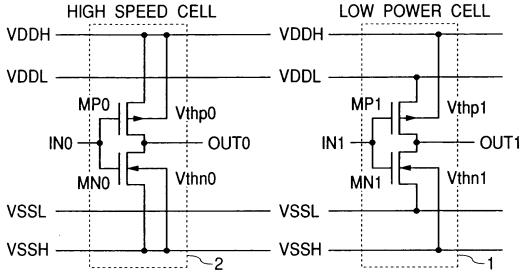
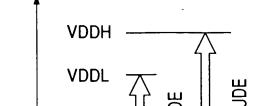


FIG. 26



[POWER POTENTIAL RELATION]

POTENTIAL VSSL VSSH 21 / 22

FIG. 27

[POWER CONNECTION OF CIRCUIT]

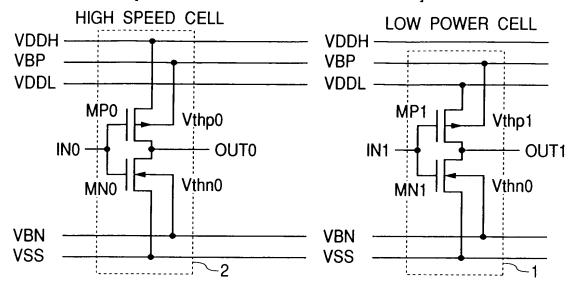
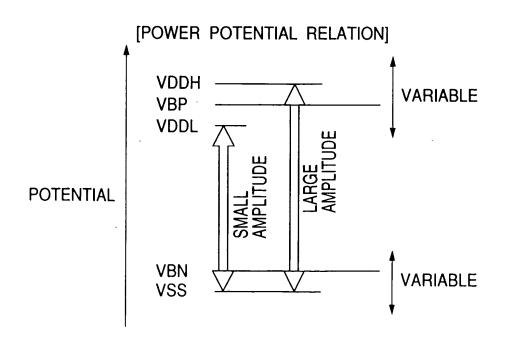


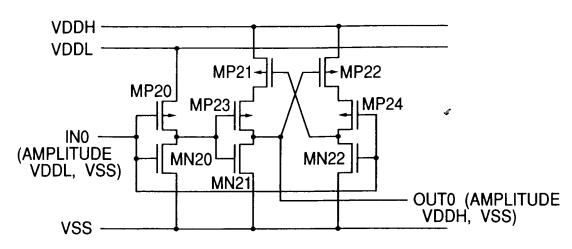
FIG. 28



The first that the time that the time that the time that

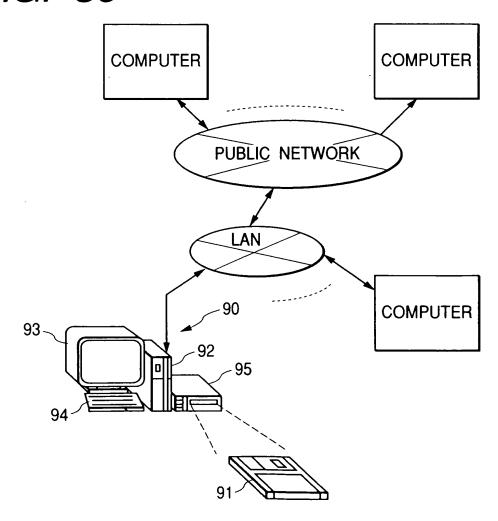
The fair wife the wife flat

FIG. 29



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FIG. 30



<u>|</u>